Eric TourniÃ©

List of Publications by Year in descending order

293 papers	5,163 citations	87888 38 h-index	175258 52 g-index
300 all docs	300 docs citations	300 times ranked	3636 citing authors

#	Article	IF	Citations
1	Crystal Phase Control during Epitaxial Hybridization of IIIâ€V Semiconductors with Silicon. Advanced Electronic Materials, 2022, 8, 2100777.	5.1	18
2	Impact of the ridge etchingâ€depth on GaSbâ€based laser diodes. Electronics Letters, 2022, 58, 162-163.	1.0	0
3	Characterization and Simulation of AlGaAsSb/GaSb Tandem Solar Cell. IEEE Journal of Photovoltaics, 2022, 12, 968-975.	2.5	1
4	Mid-infrared IIIâ€"V semiconductor lasers epitaxially grown on Si substrates. Light: Science and Applications, 2022, 11, .	16.6	20
5	Investigation of AlInAsSb/GaSb tandem cells â€" A first step towards GaSb-based multi-junction solar cells. Solar Energy Materials and Solar Cells, 2021, 219, 110795.	6.2	9
6	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. Optics Express, 2021, 29, 11268.	3.4	9
7	Thermal performance of GaInSb quantum well lasers for silicon photonics applications. Applied Physics Letters, 2021, 118, .	3.3	4
8	Near-Field Thermophotovoltaic Conversion with High Electrical Power Density and Cell Efficiency above 14%. Nano Letters, 2021, 21, 4524-4529.	9.1	79
9	Carrier recombination and temperature-dependence of GaInSb quantum well lasers for silicon photonics applications. , 2021, , .		0
10	Modeling and Characterization of an MBE-Grown Concentrator P-N GaSb Solar Cells Using a Pseudo-3D Model. IEEE Journal of Photovoltaics, 2021, 11, 1032-1039.	2.5	1
11	Selective Area Growth by Hydride Vapor Phase Epitaxy and Optical Properties of InAs Nanowire Arrays. Crystal Growth and Design, 2021, 21, 5158-5163.	3.0	5
12	Quantum well interband semiconductor lasers highly tolerant to dislocations. Optica, 2021, 8, 1397.	9.3	14
13	Carrier Recombination Processes in 2.3-Âµm Epitaxially Grown Mid-Infrared Laser Diodes on Si(001). , 2021, , .		0
14	Molecular-beam epitaxy of GaSb on 6Â°-offcut (0â€¯0â€¯1) Si using a GaAs nucleation layer. Journal of Crystal Growth, 2020, 529, 125299.	1.5	6
15	Interband mid-infrared lasers. , 2020, , 91-130.		7
16	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. Semiconductor Science and Technology, 2020, 35, 025024.	2.0	3
17	Progress in Interband Cascade Lasers: From Edge Emitting Lasers to VCSELs. , 2020, , .		0
18	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. APL Photonics, 2020, 5, .	5.7	22

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19	Morphological Control of InN Nanorods by Selective Area Growthâ€"Hydride Vapor-Phase Epitaxy. Crystal Growth and Design, 2020, 20, 2232-2239.	3.0	5
20	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. Physical Review Materials, 2020, 4, .	2.4	23
21	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. Optics Express, 2020, 28, 20785.	3.4	9
22	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. Optica, 2020, 7, 263.	9.3	42
23	3.3 Âµm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. Semiconductor Science and Technology, 2020, 35, 125029.	2.0	6
24	Improved efficiency of GaSb solar cells using an Al0.50Ga0.50As0.04Sb0.96 window layer. Solar Energy Materials and Solar Cells, 2019, 200, 110042.	6.2	14
25	The Interaction of Extended Defects as the Origin of Step Bunching in Epitaxial IIIâ€"V Layers on Vicinal Si(001) Substrates. Physica Status Solidi - Rapid Research Letters, 2019, 13, 1900290.	2.4	3
26	GaSbBi Alloys and Heterostructures: Fabrication and Properties. Springer Series in Materials Science, 2019, , 125-161.	0.6	1
27	Molecular-beam epitaxy of GaInSbBi alloys. Journal of Applied Physics, 2019, 126, .	2.5	6
28	Indium antimonide photovoltaic cells for near-field thermophotovoltaics. Solar Energy Materials and Solar Cells, 2019, 203, 110190.	6.2	15
29	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. Journal of Applied Physics, 2019, 125, .	2.5	16
30	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. JETP Letters, 2019, 109, 96-101.	1.4	4
31	Selective growth of ordered hexagonal InN nanorods. CrystEngComm, 2019, 21, 2702-2708.	2.6	13
32	Massless Dirac fermions in III-V semiconductor quantum wells. Physical Review B, 2019, 99, .	3.2	14
33	Toward MIR VCSELs operating in CW at RT. , 2019, , .		0
34	InAs/GaSb thin layers directly grown on nominal (0â€¯0â€¯1)-Si substrate by MOVPE for the fabrication of InAs FINFET. Journal of Crystal Growth, 2019, 510, 18-22.	1.5	3
35	GaSb-based solar cells for multi-junction integration on Si substrates. Solar Energy Materials and Solar Cells, 2019, 191, 444-450.	6.2	13
36	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. Infrared Physics and Technology, 2019, 96, 39-43.	2.9	29

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37	Micron-sized liquid nitrogen-cooled indium antimonide photovoltaic cell for near-field thermophotovoltaics. Optics Express, 2019, 27, A11.	3.4	31
38	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 33â€…Âµm. Optics Express, 2019, 27, 31425.	3.4	10
39	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. Applied Physics Letters, 2018, 112, .	3.3	14
40	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. Acta Materialia, 2018, 143, 121-129.	7.9	12
41	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. Thin Solid Films, 2018, 645, 5-9.	1.8	18
42	Pedestal formation of all-semiconductor gratings through GaSb oxidation for mid-IR plasmonics. Journal Physics D: Applied Physics, 2018, 51, 015104.	2.8	5
43	Quantum cascade lasers grown on silicon. , 2018, , .		0
44	Investigation of antimonide-based semiconductors for high-efficiency multi-junction solar cells. , 2018, , .		4
45	Interface energy analysis of IIIâ€“V islands on Si (001) in the Volmer-Weber growth mode. Applied Physics Letters, 2018, 113, .	3.3	14
46	Epitaxial Integration of Antimonide-Based Semiconductor Lasers on Si. Semiconductors and Semimetals, 2018, , 1-25.	0.7	2
47	A Stressâ€Free and Textured GaP Template on Silicon for Solar Water Splitting. Advanced Functional Materials, 2018, 28, 1801585.	14.9	22
48	In situ determination of the growth conditions of GaSbBi alloys. Journal of Crystal Growth, 2018, 495, 9-13.	1.5	7
49	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. Applied Surface Science, 2018, 451, 241-249.	6.1	12
50	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. Physical Review B, 2018, 97, .	3.2	24
51	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. Semiconductor Science and Technology, 2018, 33, 094006.	2.0	4
52	GaSb Lasers Grown on Silicon Substrate for Telecom Applications. , 2018, , 625-635.		2
53	Mid-IR plasmonic compound with gallium oxide toplayer formed by GaSb oxidation in water. Semiconductor Science and Technology, 2018, 33, 095009.	2.0	3
54	Quantum cascade lasers grown on silicon. Scientific Reports, 2018, 8, 7206.	3.3	56

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55	Universal description of III-V/Si epitaxial growth processes. Physical Review Materials, 2018, 2, .	2.4	43
56	AlInAsSb for GaSb-based multi-junction solar cells. , 2018, , .		3
57	LACBED analysis of the chemical composition of compound semiconductor strained layers. , 2018, , 221-224.		0
58	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. Scripta Materialia, 2017, 132, 5-8.	5.2	9
59	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. Journal of Crystal Growth, 2017, 477, 65-71.	1.5	15
60	Growth and characterization of AlInAsSb layers lattice-matched to GaSb. Journal of Crystal Growth, 2017, 477, 72-76.	1.5	9
61	GaSbBi/GaSb quantum well laser diodes. Applied Physics Letters, 2017, 110, .	3.3	45
62	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. Journal of Crystal Growth, 2017, 477, 144-148.	1.5	39
63	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. Nanophotonics, 2017, 7, 507-516.	6.0	33
64	III-V lasers epitaxially grown on Si. , 2017, , .		0
65	From 1-dimensional to 2-dimensional periodic semiconductor plasmonic resonators: Designing the optical response for sensing applications. , 2017, , .		0
66	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs â€œThree-Layerâ€•Gapless Quantum Wells. JETP Letters, 2017, 106, 727-732.	1.4	5
67	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. Optical Materials Express, 2017, 7, 3011.	3.0	14
68	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. Optics Express, 2017, 25, 26651.	3.4	15
69	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. APL Photonics, 2017, 2, .	5.7	36
70	Plasmonic bio-sensing based on highly doped semiconductors. , 2017, , .		2
71	Anisotropic strain relaxation and growth mode dependence in highly lattice mismatched III-V systems. , 2017, , 389-392.		0
72	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared. Proceedings of SPIE, 2016, , .	0.8	1

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73	Metamorphic IIIâ€"V semiconductor lasers grown on silicon. MRS Bulletin, 2016, 41, 218-223.	3.5	47
74	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. Nanotechnology, 2016, 27, 425201.	2.6	23
75	GaSb lasers grown on Silicon substrate emitting in the telecom wavelength range. , 2016, , .		0
76	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. Journal of Crystal Growth, 2016, 439, 33-39.	1.5	32
77	Terahertz studies of 2D and 3D topological transitions. Journal of Physics: Conference Series, 2015, 647, 012037.	0.4	0
78	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1â^'XAsSb waveguides. Applied Physics Letters, 2015, 107, .	3.3	15
79	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55-<i>Î¼</i>m. Applied Physics Letters, 2015, 106, .	3.3	12
80	Observation of Fano resonances in highly doped semiconductors plasmonic resonators (Presentation) Tj ETQq0 0 0 rgBT /Overlock 10 Tf	0.8	0
81	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. Optics Express, 2015, 23, 29423.	3.4	10
82	Silicon surface preparation for III-V molecular beam epitaxy. Journal of Crystal Growth, 2015, 413, 17-24.	1.5	27
83	M-lines characterization of the refractive index of GaSb and AlXGa1-XAsSb lattice-matched onto GaSb in the mid-infrared. , 2015, , .		0
84	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. Optics Express, 2014, 22, 27300.	3.4	26
85	Brewster â€œmodeâ€•in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. Optics Express, 2014, 22, 24294.	3.4	54
86	Long-wavelength silicon photonic integrated circuits. , 2014, , .		0
87	Silicon-Based Photonic Integration Beyond the Telecommunication Wavelength Range. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 394-404.	2.9	106
88	Recombination channels in 2.4â€"3.2 Âµm GaInAsSb quantum-well lasers. Semiconductor Science and Technology, 2013, 28, 015015.	2.0	17
89	Mid-IR heterogeneous silicon photonics. Proceedings of SPIE, 2013, , .	0.8	2
90	Mid-IR GaSb-Based Bipolar Cascade VCSELs. IEEE Photonics Technology Letters, 2013, 25, 882-884.	2.5	14

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91	Effects of low temperature on the cold start gaseous emissions from light duty vehicles fuelled by ethanol-blended gasoline. Applied Energy, 2013, 102, 44-54.	10.1	140
92	All-semiconductor plasmonics for mid-IR applications. , 2013, , .		3
93	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. Optics Express, 2013, 21, 6101.	3.4	82
94	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. Optical Materials Express, 2013, 3, 1523.	3.0	65
95	Mid-IR GaSb-based monolithic vertical-cavity surface-emitting lasers. Journal Physics D: Applied Physics, 2013, 46, 495101.	2.8	6
96	GaSb-based all-semiconductor mid-IR plasmonics. , 2013, , .		3
97	Integrated thin-film GaSb-based Fabry-Perot lasers: towards a fully integrated spectrometer on a SOI waveguide circuit. , 2013, , .		5
98	Atomic structure of tensile-strained GaAs/GaSb(001) nanostructures. Applied Physics Letters, 2013, 102, .	3.3	7
99	Silicon-on-Insulator spectrometers with integrated GaInAsSb photodiode array for wideband operation from 1500 to 2300 nm.. , 2013, , .		0
100	Selective lateral etching of InAs/GaSb tunnel junctions for mid-infrared photonics. Semiconductor Science and Technology, 2012, 27, 085011.	2.0	8
101	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. Optics Express, 2012, 20, 11665.	3.4	51
102	Single-Mode Monolithic GaSb Vertical-Cavity Surface-Emitting Laser. Optics Express, 2012, 20, 15540.	3.4	22
103	Localized surface plasmon resonances in highly doped semiconductors nanostructures. Applied Physics Letters, 2012, 101, .	3.3	58
104	Integrated spectrometer and integrated detectors on Silicon-on-Insulator for short-wave infrared applications. , 2012, , .		1
105	High temperature continuous wave operation of Sb-based monolithic EP-VCSEL with Selectively Etched Tunnel-Junction Apertures. , 2012, , .		0
106	Mid-Infrared Semiconductor Lasers. Semiconductors and Semimetals, 2012, , 183-226.	0.7	42
107	Pseudo volume plasmon in arrays of doped and un-doped semiconductors. Applied Physics A: Materials Science and Processing, 2012, 109, 927-934.	2.3	0
108	Arrays of doped and un-doped semiconductors for sensor applications. Applied Physics A: Materials Science and Processing, 2012, 109, 943-947.	2.3	3

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109	Online characterization of regulated and unregulated gaseous and particulate exhaust emissions from two-stroke mopeds: A chemometric approach. Analytica Chimica Acta, 2012, 717, 28-38.	5.4	39
110	GaSb-based integrated lasers and photodetectors on a Silicon-On-Insulator waveguide circuit for sensing applications in the shortwave infrared. , 2012, , .		6
111	GaSb-based laser monolithically grown on Si substrate by molecular beam epitaxy. , 2012, , .		0
112	IIIâ€"V/Silicon Photonics for Short-Wave Infrared Spectroscopy. IEEE Journal of Quantum Electronics, 2012, 48, 292-298.	1.9	8
113	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. IEEE Photonics Technology Letters, 2011, 23, 1760-1762.	2.5	34
114	Note: A high transmission Faraday optical isolator in the 9.2 Î¼m range. Review of Scientific Instruments, 2011, 82, 096106.	1.3	8
115	Heterogeneous GaSb/SOI mid-infrared photonic integrated circuits for spectroscopic applications. , 2011, , .		3
116	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. Applied Physics Letters, 2011, 99, .	3.3	78
117	Heterogeneously integrated InGaAsSb detectors on SOI waveguide circuits for short-wave infrared applications. , 2011, , .		0
118	Non-random Be-to-Zn substitution in ZnBeSe alloys: Raman scattering and ab initio calculations. European Physical Journal B, 2010, 73, 461-469.	1.5	9
119	Sb-based laser sources grown by molecular beam epitaxy on silicon substrates. Proceedings of SPIE, 2010, , .	0.8	0
120	Interfacial intermixing in InAs/GaSb short-period-superlattices grown by molecular beam epitaxy. Applied Physics Letters, 2010, 96, .	3.3	44
121	Highly tensile-strained, type-II, Ga1â^'xInxAs/GaSb quantum wells. Applied Physics Letters, 2010, 96, .	3.3	12
122	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 mum at Room Temperature. IEEE Photonics Technology Letters, 2010, 22, 553-555.	2.5	67
123	Optical performances of InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission. Journal of Applied Physics, 2010, 108, 093107.	2.5	14
124	Modelling of an InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission by the k.p method. Journal Physics D: Applied Physics, 2010, 43, 325102.	2.8	14
125	GaSb-based mid-IR electrically-pumped VCSELs covering the wavelength range from 2.3 to 2.7 µm. , 2009, , .		0
126	InAs/GaSb/InSb short-period super-lattice diode lasers emitting near 3.3â€…[micro sign]m at room-temperature. Electronics Letters, 2009, 45, 165.	1.0	11

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127	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. Journal of Crystal Growth, 2009, 311, 1739-1744.	1.5	23
128	MBE growth of mid-IR diode lasers based on InAs/GaSb/InSb short-period superlattice active zones. Journal of Crystal Growth, 2009, 311, 1905-1907.	1.5	6
129	GaSb-based VCSELs emitting in the mid-infrared wavelength range (2â€“3Î¼m) grown by MBE. Journal of Crystal Growth, 2009, 311, 1912-1916.	1.5	29
130	Mid-infrared GaSb-based EP-VCSEL emitting at 2.63â€…[micro sign]m. Electronics Letters, 2009, 45, 265.	1.0	33
131	Room-temperature operation of a 2.25â€‚Î¼m electrically pumped laser fabricated on a silicon substrate. Applied Physics Letters, 2009, 94, .	3.3	37
132	Mid-IR lasing from highly tensile-strained, type II, GaInAs/GaSb quantum wells. Electronics Letters, 2009, 45, 1320.	1.0	5
133	GaSb-based, 2.2â€‚Î¼m type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. Applied Physics Letters, 2009, 94, 023506.	3.3	40
134	Room temperature, continuous wave operation of an Sb-based laser grown on GaAs substrate. , 2009, , .		0
135	Demonstration of laser operation at room-temperature of an Sb-based mid-infrared multi-quantum-well structure monolithically grown on a Silicon substrate. , 2009, , .		0
136	Subpicosecond timescale carrier dynamics in GaInAsSbâˆ•AlGaAsSb double quantum wells emitting at 2.3Î¼m. Applied Physics Letters, 2008, 92, .	3.3	20
137	S20 photocathodes grown by molecular-beam deposition. Electronics Letters, 2008, 44, 315.	1.0	1
138	Type II transition in InSb-based nanostructures for midinfrared applications. Journal of Applied Physics, 2008, 103, 114516.	2.5	9
139	Transmission Electron Microscopy Study of Sb-Based Quantum Dots. Springer Proceedings in Physics, 2008, , 251-254.	0.2	0
140	InAs/GaSb short-period superlattice injection lasers operating in 2.5â€…[micro sign]mâ€“3.5â€…[micro sign]m mid-infrared wavelength range. Electronics Letters, 2007, 43, 1285.	1.0	15
141	Conduction-band crossover induced by misfit strain in<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi mathvariant="normal">In</mml:mi><mml:mi mathvariant="normal">Sb</mml:mi><mml:mo>âˆ•</mml:mo><mml:mi mathvariant="normal">Ga</mml:mi><mml:mi mathvariant="normal">Sb</mml:mi></mml:mrow></mml:math>self-assembled quantum dots. Physical R	3.2	9
142	Molecular-beam epitaxy of InSb/GaSb quantum dots. Journal of Applied Physics, 2007, 101, 124309.	2.5	31
143	High-density InSb-based quantum dots emitting in the mid-infrared. Journal of Crystal Growth, 2007, 301-302, 713-717.	1.5	18
144	Growth and characterization of GaInSb/GaInAsSb hole-well laser diodes emitting near 2.93Î¼m. Journal of Crystal Growth, 2007, 301-302, 967-970.	1.5	3

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145	Interface analysis of InAs/GaSb superlattice grown by MBE. Journal of Crystal Growth, 2007, 301-302, 889-892.	1.5	47
146	Investigations of InSb-based quantum dots grown by molecular-beam epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 1743-1746.	0.8	1
147	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. Physica Status Solidi (B): Basic Research, 2007, 244, 2683-2696.	1.5	11
148	Structural and optical properties of InSb quantum dots for mid-IR applications. Physica Status Solidi (B): Basic Research, 2006, 243, 3959-3962.	1.5	8
149	Correlation between quantum well morphology, carrier localization and the optoelectronic properties of GaInNAs/GaAs light emitting diodes. Semiconductor Science and Technology, 2006, 21, 1047-1052.	2.0	5
150	High-density, uniform InSbâˆ•GaSb quantum dots emitting in the midinfrared region. Applied Physics Letters, 2006, 89, 263118.	3.3	26
151	720 mW continuous wave room temperature operation diode laser emitting at around 2.4 Î¼m. , 2005, 5989, 81.		1
152	LO multi-phonons cooperative phenomenon in ZnSeâ€“BeSemixed crystals. Journal of Physics and Chemistry of Solids, 2005, 66, 2099-2103.	4.0	4
153	Percolation picture for long wavelength phonons in zinc blende alloys: application to GaInAs. Journal of Physics and Chemistry of Solids, 2005, 66, 2094-2098.	4.0	0
154	Decomposition in as-grown (Ga,In)(N,As) quantum wells. Applied Physics Letters, 2005, 87, 171901.	3.3	40
155	Correlation between interface structure and light emission at 1.3â€“1.55 Î¼m of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 2195.	1.6	34
156	Long-wave phonons inZnSeâˆ'BeSemixed crystals: Raman scattering and percolation model. Physical Review B, 2004, 70, .	3.2	28
157	Beâ€“Se double-phonon behavior in Zn1âˆ'xâˆ'yMgyBexSe alloy. Journal of Applied Physics, 2004, 95, 7690-7693.	2.5	4
158	Carrier recombination processes in GaAsN: from the dilute limit to alloying. IEE Proceedings: Optoelectronics, 2004, 151, 365-368.	0.8	4
159	Percolation-based multimode Gaâ€“N behaviour in the Raman spectra of GaInAsN. IEE Proceedings: Optoelectronics, 2004, 151, 338-341.	0.8	0
160	Giant LO oscillation in the Zn1âˆ'xBex(Se,Te) multi-phonons percolative alloys. Thin Solid Films, 2004, 450, 195-198.	1.8	5
161	Does In-bonding delay GaN-segregation in GaInAsN? A Raman study. Applied Physics Letters, 2004, 85, 5872-5874.	3.3	11
162	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. Applied Physics Letters, 2004, 84, 2503-2505.	3.3	57

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163	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. Physical Review B, 2004, 69, .	3.2	34
164	Dominant carrier recombination mechanisms in GaInNAsâˆ•GaAs quantum well light-emitting diodes. Applied Physics Letters, 2004, 85, 40-42.	3.3	7
165	Bi-modal Raman response of Beâ€"Se vibration in Zn1âˆ'âˆ'Mg Be Se alloys. Journal of Alloys and Compounds, 2004, 382, 271-274.	5.5	7
166	Effect of nitrogen on the band structure and material gain of In/sub y/Ga/sub 1-y/As/sub 1-x/N/sub x/-GaAs quantum wells. IEEE Journal of Selected Topics in Quantum Electronics, 2003, 9, 716-722.	2.9	16
167	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. Journal of Crystal Growth, 2003, 251, 383-387.	1.5	31
168	Percolation context in mixed crystals with mechanical contrast. Journal of Physics and Chemistry of Solids, 2003, 64, 1585-1590.	4.0	2
169	LO phononâ€"plasmon coupling and mechanical disorder-induced effect in the Raman spectra of GaAsN alloys. Solid-State Electronics, 2003, 47, 455-460.	1.4	5
170	Photoluminescence spectroscopy of Ga(In)NAs quantum wells for emission at 1.5 Î¼m. Solid-State Electronics, 2003, 47, 477-482.	1.4	11
171	Coexistence in photoluminescence of free exciton and bound exciton in low nitrogen content GaInNAs layers. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2631-2634.	0.8	0
172	Nanoindentation of Si, GaP, GaAs and ZnSe single crystals. Journal Physics D: Applied Physics, 2003, 36, L5-L9.	2.8	74
173	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. Journal of Applied Physics, 2003, 94, 2319-2324.	2.5	60
174	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 Î¼m. Applied Physics Letters, 2003, 82, 1845-1847.	3.3	38
175	Percolation-based vibrational picture to estimate nonrandom N substitution in GaAsN alloys. Applied Physics Letters, 2003, 82, 2808-2810.	3.3	18
176	Isoelectronic traps in heavily doped GaAs:(In,N). Physical Review B, 2003, 68, .	3.2	14
177	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. Applied Physics Letters, 2003, 82, 3451-3453.	3.3	36
178	Mechanisms affecting the photoluminescence spectra of GaInNAs after post-growth annealing. Applied Physics Letters, 2002, 80, 4148-4150.	3.3	85
179	Nanoindentation study of Zn1ÂxBexSe heteroepitaxial layers. Journal Physics D: Applied Physics, 2002, 35, 3015-3020.	2.8	24
180	Raman study of Zn1âˆ'xBexSe/GaAs systems with low Be content (xâ©½0.20). Journal of Applied Physics, 2002, 91, 9187-9197.	2.5	14

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